

a semiconductor region of the second conduction type extending from the surface of the semiconductor substrate to a peripheral portion of the buried semiconductor layer, the semiconductor region of the second conduction type being connected to the buried semiconductor layer; and

a semiconductor region of the first conduction type formed in the semiconductor substrate surrounded by the buried semiconductor layer and the semiconductor region of the second conduction type, the semiconductor region of the first conduction type being isolated from the semiconductor substrate by the buried semiconductor layer and the semiconductor region of the second conduction type,

wherein a concentration of an impurity in the semiconductor region of the first conduction type is equal to a concentration of an impurity in the semiconductor substrate.

REMARKS

The Office Action dated October 4, 2002, has been received and carefully noted. The preceding amendments and the following remarks are submitted as a full and complete response thereto. Claim 1 is amended. No new matter has been added. Accordingly, claims 1-7 are pending in this application and are submitted for consideration.

Claims 1-7 were rejected under 35 U.S.C. § 103(a) as being unpatentable over the Applicants' admitted prior art (AAPA) in view of U.S. Patent No. 4,247,863 to Togei. In particular, it was asserted in the Office Action that the AAPA teaches many features